

Title	On-demand single-photons from electrically-injected site-controlled pyramidal quantum dots
Authors	Chung, Tung-Hsun;Moroni, Stefano T.;Juska, Gediminas;Gocalińska, Agnieszka M.;Pelucchi, Emanuele
Publication date	2018-11-21
Original Citation	Moroni, S. T., Chung, T. H., Juska, G., Gocalinska, A. and Pelucchi, E. (2019) 'On-demand single-photons from electrically-injected site-controlled pyramidal quantum dots', Journal of Physics D: Applied Physics, 52(4), 045107 (5 pp). doi: 10.1088/1361-6463/aaed73
Type of publication	Article (peer-reviewed)
Link to publisher's version	http://stacks.iop.org/0022-3727/52/i=4/a=045107 - 10.1088/1361-6463/aaed73
Rights	© 2018 IOP Publishing Ltd. This is an author-created, un-copyedited version of an article accepted for publication in Journal of Physics D: Applied Physics. The publisher is not responsible for any errors or omissions in this version of the manuscript or any version derived from it. The Version of Record is available online at https://doi.org/10.1088/1361-6463/aaed73 . As the Version of Record of this article has been published on a subscription basis, this Accepted Manuscript will be available for reuse under a CC BY-NC-ND 3.0 licence after a 12 month embargo period. - https://creativecommons.org/licences/by-nc-nd/3.0
Download date	2026-10-07 17:03:21
Item downloaded from	https://hdl.handle.net/10468/7247



University College Cork, Ireland
Coláiste na hOllscoile Corcaigh

ACCEPTED MANUSCRIPT

On-demand single-photons from electrically-injected site-controlled Pyramidal Quantum Dots

To cite this article before publication: Stefano Moroni *et al* 2018 *J. Phys. D: Appl. Phys.* in press <https://doi.org/10.1088/1361-6463/aaed73>

Manuscript version: Accepted Manuscript

Accepted Manuscript is "the version of the article accepted for publication including all changes made as a result of the peer review process, and which may also include the addition to the article by IOP Publishing of a header, an article ID, a cover sheet and/or an 'Accepted Manuscript' watermark, but excluding any other editing, typesetting or other changes made by IOP Publishing and/or its licensors"

This Accepted Manuscript is © 2018 IOP Publishing Ltd.

During the embargo period (the 12 month period from the publication of the Version of Record of this article), the Accepted Manuscript is fully protected by copyright and cannot be reused or reposted elsewhere.

As the Version of Record of this article is going to be / has been published on a subscription basis, this Accepted Manuscript is available for reuse under a CC BY-NC-ND 3.0 licence after the 12 month embargo period.

After the embargo period, everyone is permitted to use copy and redistribute this article for non-commercial purposes only, provided that they adhere to all the terms of the licence <https://creativecommons.org/licences/by-nc-nd/3.0>

Although reasonable endeavours have been taken to obtain all necessary permissions from third parties to include their copyrighted content within this article, their full citation and copyright line may not be present in this Accepted Manuscript version. Before using any content from this article, please refer to the Version of Record on IOPscience once published for full citation and copyright details, as permissions will likely be required. All third party content is fully copyright protected, unless specifically stated otherwise in the figure caption in the Version of Record.

View the [article online](#) for updates and enhancements.

On-demand single-photons from electrically-injected site-controlled Pyramidal Quantum Dots

S. T. Moroni, T. H. Chung, G. Juska, A. Gocalinska, and E. Pelucchi

Tyndall National Institute, University College Cork, Dyke Parade, Cork, Ireland

Abstract

We report on the performance of electrically-injected Pyramidal Quantum Dots in terms of single-photon emission. We previously presented the generation of entangled photon pairs from similarly structured devices. Here we show that it is also possible to obtain single-photons upon continuous wave excitation as well as pulsed excitation, obtaining a low $g^2(0)$ of 0.088 ± 0.059 , by discarding re-excitation events within a single excitation pulse by applying time-gating techniques.

1. Introduction

Integration, scalability, reproducibility and high quantum state fidelities: these are some of the main technological challenges to be tackled in order to achieve a realistic source of photons to be employed in quantum computation [1][2]. Semiconductor quantum dot (QD)-based light sources have recently been gaining great relevance in this perspective, as they can be employed for the generation of quantum light while allowing for processing by means of standard semiconductor-based fabrication and integration techniques. Semiconductor QDs have been demonstrated as sources of single photons [3][4][5], highly indistinguishable photons[6][7], entangled photon pairs with high fidelity[8][9][10], time-bin entangled photons [11] and more, thanks to their versatility and tunability. In addition to this, among the requirements for a QD-based technology for quantum computation, efficient electrical injection would allow an extremely simplified excitation scheme and therefore easier QD integration.

Electroluminescence from semiconductor QDs has been reportedly achieved in the past[12], together with electrically driven single photon emission[13][14] and entangled photon emission[9][15], but only a few reported cases claimed to be site controlled as well[16][17]. Although, in most of these cases, it was generally about the possibility to statistically control the self-assembled QDs position, while the only instance of true deterministic site control of the electrically driven QDs was based on Pyramidal Quantum Dots (PQDs)[18][19], but without proof of single photon emission. Note also that references [18][19] discuss two different pyramidal site controlled material systems, each showing different challenges of their own, one based on AlGaAs barriers [20], the other on GaAs barriers.

Here we report for the first time on the possibility of generating single photons by embedding PQDs into a PIN-junction device, a structure largely similar to previous designs for entangled photon emission reported in [19], and therefore proving single photon electrically driven emission from a true site-controlled QD system. Besides the statistic regarding directly single-photon emission quality, we find that our analysis also provides interesting insight on the ability of filtering photon detection events to improve the performance of our devices. Our findings suggest, after a comparison with previous work on entangled-photon emission through electrical injection, that a good entangled photon emitter from QDs is not necessarily also a good single photon emitter (and, obviously, vice versa). We address this point more in detail further in our contribution.

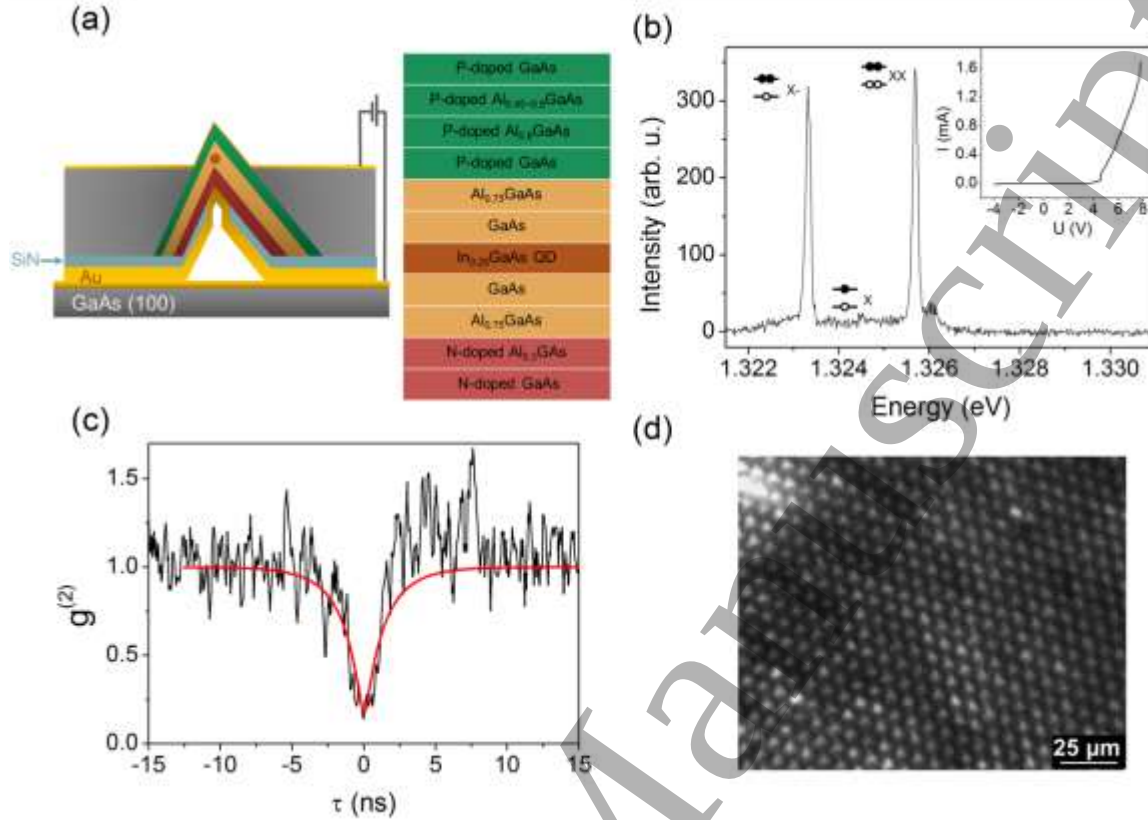


Fig.1: a) a sketch of a structure of a P-QD-based LED; b) representative spectrum from an electrically injected P-QD, showing a dominant X- behavior and an almost suppressed X and (inset) typical IV response of a P-QD-based LED; c) autocorrelation for the X- transition from an electrically-driven P-QD under DC bias excitation (black line) and fitting of the data using a $g^2(\tau)$ function convoluted with the response function for the measurement apparatus; d) CCD image of lit P-QD-LEDs under DC bias excitation.

2. Fabrication and characterization methods

PQDs are fabricated starting from a (111)B GaAs wafer using a lithography based patterning technique to form an ordered array of inverted pyramidal recesses; Metalorganic Vapor Phase Epitaxy is then performed, allowing for the site control of the QDs, one for each recess. More recently we developed a more advanced type of device design for the realization of electrical injection. As detailed elsewhere [19], the QD is embedded into the intrinsic region of the PIN junction, whose detailed structure is reported in the supplementary material. The complex geometry and copiousness of nanostructure formation (e.g. lateral quantum wires formed along the edges of the pyramidal recess and lateral quantum wells formed along its sidewalls, see [21] and references therein) of the pyramidal system makes it necessary to perform a number of processing steps to achieve the proper electrical contacting of the devices: insulation of the corners of the pyramid, masking of the insulation through tilted Au evaporation, selective removal of the insulation, P-side contacting, back-etching [22], and N-side contacting. For

simplicity of fabrication, the scheme relies on the simultaneous contacting of all the pyramidal QD devices, which share the same top and bottom contacts and therefore share the same applied electrical bias. Henceforth the electrical properties of the device we will refer to in this paper will be the total ensemble current vs. voltage characteristics. A typical I-V curve for one of our devices is shown in Fig.1b (inset), where it can be seen that the exponential rise in the current is obtained at about 6 V.

It is worth underling at this point the possible origin of the high turn-on voltage in our devices, compared to similar LED devices[23][9]. On one hand, the metal used for the metallization of the GaAs P-doped layer is not ideal and might be causing a Schottky barrier [24]. On the other hand, the carriers have to be channeled through a Ga-rich AlGaAs vertical quantum wire with a very small cross-section (<40 nm diameter through the centre of the pyramid)[19], which might cause a high resistance, although forcing the carrier through the centre of the structure, towards the QD. It is also relevant to note that different QDs could show different turn-on voltages: this is mainly due to the spread in etching depth of the original GaAs substrate on the top of each pyramid, resulting from the back-etching process. Each pyramidal structure presents a slightly different open area on the N-doped region for contacting, therefore leading to a distribution of surface resistances, from which the difference in turn-on voltages.

The QDs were analyzed by low-temperature (10K) micro-electroluminescence spectroscopy using a 100x magnification objective with a numerical aperture of 0.8, allowing for the spatial filtering of the light coming from different PQDs (which had a spacing of 10 μm) simply by scanning on the sample surface by means of piezoelectric actuators. Although the turn-on voltage was slightly different for each individual PQD diode, this was typically around 6 V; voltage at which it was possible to detect excitonic transitions.

3. Results and discussion

Fig.1b shows a representative spectrum from an electrically injected PQD under DC excitation. We identify each transition as exciton (X), biexciton (XX) and a negatively charged exciton (X⁻; based on previous results [25] where negatively charged excitons and positively charged excitons were systematically identified also by employing a second wavelength excitation for the release of extra holes in the surrounding of the QD), which is typically the predominant transition in terms of intensity. In some cases the exciton was completely suppressed by the excess of negative charges[25]. When operating in DC, it was possible to obtain single-photons from the X⁻ transition, for example. We chose this transition to test for single photon emission mostly as it was the brightest transition of the excitonic ensemble, typically showing at least 3 times the exciton overall intensity, but also because the trion transition is ideally the more suited for single photon emission, not being subject to special selection rules [26]. Moreover, the X⁻ transition is more suitable for the generation of indistinguishable photons, as it is not affected by a fine structure splitting and therefore more often studied for indistinguishability studies (see for example [27]).

A standard HBT setup was employed for autocorrelation measurement. One representative case is shown in Fig.1c. Upon the application of 6.8 V, the $g^2(0)$ autocorrelation function reaches 0.17, which has been fitted taking into account the detector response function (a Gaussian response with 400 ps FWHM).

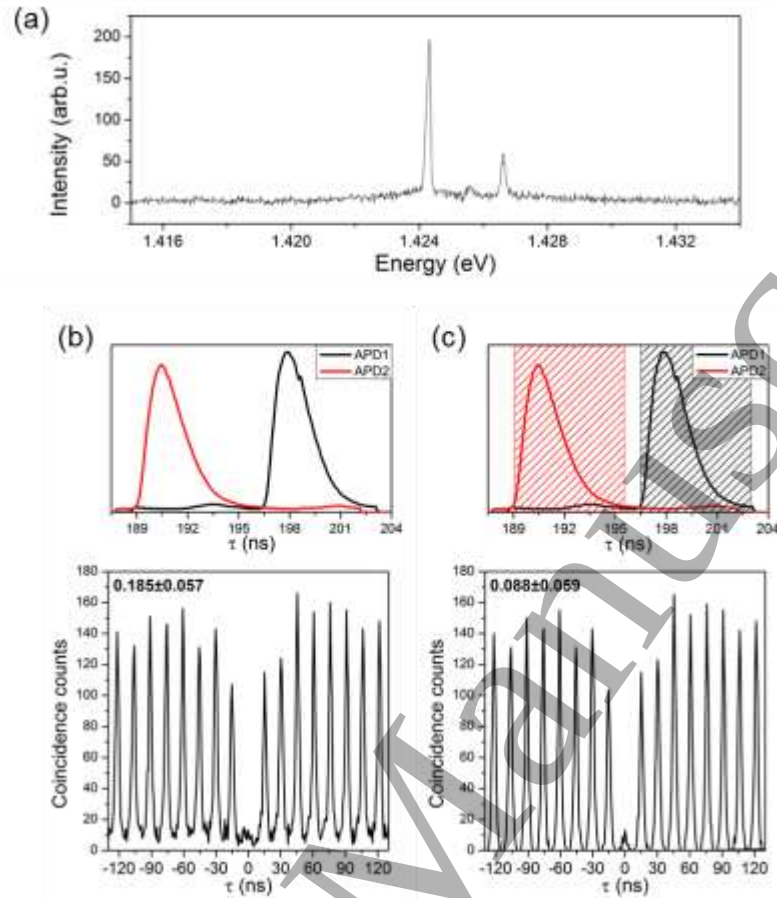


Fig.2: a) Emission dynamics of a PQR under pulsed electrical injection; b) to c) lifetime measurement for the two detectors employed (top) and autocorrelation measurement (bottom) in pulsed excitation selecting different time windows (highlighted in the top graph) within one excitation pulse period for the time gating filtering process: all detection events are selected in b), second-pulses events are discarded in c) by selecting a time window of 6.5 ns; the resulting $g^2(0)$ for each case is shown in the inset of the corresponding graph.

In order to operate the device in pulsed excitation - and prove on demand generation of single photons - we applied a DC bias on the top of which we superimposed the AC pulses. From the I-V curve we can deduce the resistance of the device when the turn-on has been reached, which falls in the $k\Omega$ range. This high resistance causes a high impedance mismatch between the LEDs and the pulse generator (which has a standard 50Ω output resistance). The mismatch could result in reflections of the signal at the device and re-excitation pulses. Since individual QDs had diverse turn-on voltages, different settings of the pulse generator (frequency, DC and AC voltages) resulted in different behaviors of the device in terms e.g. of intensity of the spectrum features and single-photon emission performance. For instance, an inefficient or insufficiently high excitation level leads to a low-intensity spectrum, while an excessive population of the QD would result in a quick re-excitation of the same transition. At different DC and AC voltage levels the whole apparatus and QD system had a different response also in terms of pulse reflections along the line, making it necessary to tune the excitation frequency as well. Therefore ad hoc settings had to be chosen

for each individual QD. Nonetheless, in most of the cases it was possible to find a set of parameters for which the PQD could be operated in pulsed excitation in a good regime for single-photon emission.

Fig. 2 shows a representative case: in order to operate the device in pulsed excitation, we applied a DC bias of 0.85 V on the top of which we superimposed a pulse of 8.67 V and 1.425 ns pulse width with a frequency of 66 MHz. The autocorrelation from this type of excitation is presented in Fig.2b: $g^2(0)$ is 0.185 ± 0.057 . As it can be seen in the time-dependence in Fig.2, reflections along the line often caused a low intensity second pulse. A time-gating technique was then employed in order to discard such second pulsing event. In this case, the correlation curves were obtained by recording all photon detection events in a time tag mode, followed by a post-construction procedure of the correlation curve [28]. This method allowed testing correlations of photons from different time windows using the raw data obtained at exactly the same experimental conditions. Fig.2c shows the autocorrelation obtained by considering detection events falling only in a determined time window (*time gating*). With a 6.5 ns wide window, the $g^2(0)$ improves significantly to 0.088 ± 0.059 , which if corrected for noise levels and detectors time resolution, is effectively a very low value.

Finally, we would like to discuss briefly the different filtering approaches employed in this work and in our previous work on the electrical excitation of PQDs for entangled photon emission [19]. While in this paper we applied a standard time gating technique (as e.g. in [29]) which allows filtering the detection events based on the lifetimes to discard re-excitation events and “restore” the single photon quality, in our previous work [19] we applied a different approach. In [19] we selected a time-window from the correlation measurement itself rather than from the lifetimes, therefore filtering time events based on the direct time difference between the detection of biexciton and exciton related photons coming in sequence in the cascade. This other time-filtering technique allows selecting fast transitions between exciton and biexciton and, if a narrow enough time-window is selected, it discards biexciton re-excitation events, which is necessary but not sufficient to result in single-photon emission. Selecting photons based on the time separation of the biexciton and exciton means to discard background events coming from any type of source of contamination of the correlation and filter the photons which are part of an entangled pair even if they wouldn’t be per se single photon events. We could think of this method as of a specific filter for the selection of biexciton-exciton detection events correlated through a direct cascade. To provide an intuitive example, rapid re-excitation of biexciton might occur, followed by a recombination cascade which actually results in entangled photon pair emission, properly selected by the method employed in [19], although the biexciton second photon would degrade the single photon statistics (a similar argument might be employed for exciton re-excitation) and would be discarded in standard time-gating techniques like the one employed in this paper, depending on the selected time-window.

Although it might seem trivial, this was previously unreported for this specific case (and could effectively be useful for practical purposes), while, to some extent, has similarities to what is called, in downconversion processes, photon heralding (see e.g. [30]). The successful application of this post-selection technique used in [19] means in principle that perfect single photon emission is not required to obtain high fidelity (>0.8) entangled photons. Our conclusion is that, although perfect entangled-photon emission is definitely limited by single photon pair quality, generally, high fidelity entanglement can be obtained from non-perfect single-photon emitting devices if the correct events are selected.

4. Conclusion

In conclusion, we showed the single photon emission performance of PQDs under both DC and pulsed electrical excitation, yielding respectively a $g^2(0)$ of 0.17 and 0.185. In pulsed excitation, the application of a simple time gating technique allowed to discard re-excitation events and obtain a $g^2(0)$ of 0.088, therefore proving that it is possible in principle to achieve a high quality single photon emission from our devices. Further improvements will be the subject of future research, and could be achieved either by employing even shorter pulses or improving the overall injection of the PQD, for example reducing the contact resistance or producing smaller pyramids.

Acknowledgments

This research was supported by Science Foundation Ireland under Grant Nos. 10/IN.1/I3000, 15/IA/2864, and 12/RC/2276. The authors are grateful to Dr. K. Thomas for the MOVPE system support.

References

- [1] P. Kok, W. J. Munro, K. Nemoto, T. C. Ralph, J. P. Dowling, and G. J. Milburn, "Linear optical quantum computing with photonic qubits," *Rev. Mod. Phys.*, vol. 79, no. 1, pp. 135–174, Jan. 2007.
- [2] I. L. Chuang and D. Gottesman, "Demonstrating the viability of universal quantum computation using teleportation and single-qubit operations," *Nature*, vol. 402, no. 6760, pp. 390–393, Nov. 1999.
- [3] P. Michler, A. Kiraz, C. Becher, W. V Schoenfeld, P. M. Petroff, L. Zhang, E. Hu, and A. Imamoglu, "A quantum dot single-photon turnstile device," *Science*, vol. 290, no. 5500, pp. 2282–5, Dec. 2000.
- [4] N. Somaschi, V. Giesz, L. De Santis, J. C. Loredo, M. P. Almeida, G. Hornecker, S. L. Portalupi, T. Grange, C. Antón, J. Demory, C. Gómez, I. Sagnes, N. D. Lanzillotti-Kimura, A. Lemaître, A. Auffeves, A. G. White, L. Lanco, and P. Senellart, "Near-optimal single-photon sources in the solid state," *Nat. Photonics*, vol. 10, no. 5, pp. 340–345, May 2016.
- [5] L. Schweickert, K. D. Jöns, K. D. Zeuner, S. F. Covre da Silva, H. Huang, T. Lettner, M. Reindl, J. Zichi, R. Trotta, A. Rastelli, and V. Zwiller, "On-demand generation of background-free single photons from a solid-state source," *Appl. Phys. Lett.*, vol. 112, no. 9, p. 093106, Feb. 2018.
- [6] C. Santori, D. Fattal, J. Vučković, G. S. Solomon, and Y. Yamamoto, "Indistinguishable photons from a single-photon device," *Nature*, vol. 419, no. 6907, pp. 594–597, Oct. 2002.
- [7] H. Wang, Z.-C. Duan, Y.-H. Li, S. Chen, J.-P. Li, Y.-M. He, M.-C. Chen, Y. He, X. Ding, C.-Z. Peng, C. Schneider, M. Kamp, S. Höfling, C.-Y. Lu, and J.-W. Pan, "Near-Transform-Limited Single Photons from an Efficient Solid-State Quantum Emitter," *Phys. Rev. Lett.*, vol. 116, no. 21, p. 213601, May 2016.
- [8] N. Akopian, N. H. Lindner, E. Poem, Y. Berlatzky, J. Avron, D. Gershoni, B. D. Gerardot, and P.

- M. Petroff, "Entangled Photon Pairs from Semiconductor Quantum Dots," *Phys. Rev. Lett.*, vol. 96, no. 13, p. 130501, Apr. 2006.
- [9] C. L. Salter, R. M. Stevenson, I. Farrer, C. A. Nicoll, D. A. Ritchie, and A. J. Shields, "An entangled-light-emitting diode," *Nature*, vol. 465, no. 7298, pp. 594–597, 2010.
- [10] D. Huber, M. Reindl, Y. Huo, H. Huang, J. S. Wildmann, O. G. Schmidt, A. Rastelli, and R. Trotta, "Highly indistinguishable and strongly entangled photons from symmetric GaAs quantum dots," *Nat. Commun.*, vol. 8, p. 15506, May 2017.
- [11] M. A. M. Versteegh, M. E. Reimer, A. A. van den Berg, G. Juska, V. Dimastrodonato, A. Gocalinska, E. Pelucchi, and V. Zwiller, "Single pairs of time-bin-entangled photons," *Phys. Rev. A*, vol. 92, no. 3, p. 033802, Sep. 2015.
- [12] A. Boretti, L. Rosa, A. Mackie, and S. Castelletto, "Electrically Driven Quantum Light Sources," *Adv. Opt. Mater.*, vol. 3, no. 8, pp. 1012–1033, Aug. 2015.
- [13] Z. Yuan, B. E. Kardynal, R. M. Stevenson, A. J. Shields, C. J. Lobo, K. Cooper, N. S. Beattie, D. A. Ritchie, and M. Pepper, "Electrically driven single-photon source," *Science*, vol. 295, no. 5552, pp. 102–5, Jan. 2002.
- [14] F. Hargart, C. A. Kessler, T. Schwarzbäck, E. Koroknay, S. Weidenfeld, M. Jetter, and P. Michler, "Electrically driven quantum dot single-photon source at 2 GHz excitation repetition rate with ultra-low emission time jitter," *Appl. Phys. Lett.*, vol. 102, no. 1, p. 011126, Jan. 2013.
- [15] J. Zhang, J. S. Wildmann, F. Ding, R. Trotta, Y. Huo, E. Zallo, D. Huber, A. Rastelli, and O. G. Schmidt, "High yield and ultrafast sources of electrically triggered entangled-photon pairs based on strain-tunable quantum dots," *Nat. Commun.*, vol. 6, p. 10067, Dec. 2015.
- [16] W. Unrau, D. Quandt, J.-H. Schulze, T. Heindel, T. D. Germann, O. Hitzemann, A. Strittmatter, S. Reitzenstein, U. W. Pohl, and D. Bimberg, "Electrically driven single photon source based on a site-controlled quantum dot with self-aligned current injection," *Appl. Phys. Lett.*, vol. 101, no. 21, p. 211119, Nov. 2012.
- [17] M. Mehta, D. Reuter, A. Melnikov, A. D. Wieck, S. Michaelis de Vasconcellos, T. Baumgarten, A. Zrenner, and C. Meier, "Intentionally positioned self-assembled InAs quantum dots in an electroluminescent p-i-n junction diode," *Phys. E Low-dimensional Syst. Nanostructures*, vol. 42, no. 10, pp. 2749–2752, Sep. 2010.
- [18] M. H. Baier, C. Constantin, E. Pelucchi, and E. Kapon, "Electroluminescence from a single pyramidal quantum dot in a light-emitting diode," *Appl. Phys. Lett.*, vol. 84, no. 11, pp. 1967–1969, Mar. 2004.
- [19] T. H. Chung, G. Juska, S. T. Moroni, A. Pescaglini, A. Gocalinska, and E. Pelucchi, "Selective carrier injection into patterned arrays of pyramidal quantum dots for entangled photon light-emitting diodes," *Nat. Photonics*, vol. 10, no. 12, pp. 782–787, Oct. 2016.
- [20] E. Pelucchi, M. Baier, Y. Ducommun, S. Watanabe, and E. Kapon, "High-quality In_xGa_{1-x}As/Al_{0.30}Ga_{0.70}As quantum dots grown in inverted pyramids," *Phys. Status Solidi B-Basic Solid State Phys.*, vol. 238, no. 2, pp. 233–236, 2003.
- [21] G. Juska, V. Dimastrodonato, L. O. Mereni, T. H. Chung, A. Gocalinska, E. Pelucchi, B. Van Hattem, M. Ediger, and P. Corfdir, "Complex optical signatures from quantum dot nanostructures

- and behavior in inverted pyramidal recesses,” *Phys. Rev. B*, vol. 89, no. 20, p. 205430, May 2014.
- [22] L. O. Mereni, V. Dimastrodonato, R. J. Young, and E. Pelucchi, “A site-controlled quantum dot system offering both high uniformity and spectral purity,” *Appl. Phys. Lett.*, vol. 94, no. 22, p. 223121, Jun. 2009.
- [23] J. Zhang, F. Ding, E. Zallo, R. Trotta, B. Höfer, L. Han, S. Kumar, Y. Huo, A. Rastelli, and O. G. Schmidt, “A nanomembrane-based wavelength-tunable high-speed single-photon-emitting diode,” *Nano Lett.*, vol. 13, no. 12, pp. 5808–13, Jan. 2013.
- [24] D. R. Lovell, T. Yamamoto, M. Inai, T. Takebe, and K. Kobayashi, “Titanium/Gold Schottky Contacts on P-Type GaAs Grown on (111)A and (100) GaAs Substrates Using Molecular Beam Epitaxy,” *Jpn. J. Appl. Phys.*, vol. 31, no. Part 2, No. 7B, pp. L924–L927, Jul. 1992.
- [25] G. Juska, E. Murray, V. Dimastrodonato, T. H. Chung, S. T. Moroni, A. Gocalinska, and E. Pelucchi, “Conditions for entangled photon emission from (111)B site-controlled pyramidal quantum dots,” *J. Appl. Phys.*, vol. 117, no. 13, p. 134302, Apr. 2015.
- [26] M. Reischle, G. J. Beirne, R. Roßbach, M. Jetter, and P. Michler, “Influence of the Dark Exciton State on the Optical and Quantum Optical Properties of Single Quantum Dots,” *Phys. Rev. Lett.*, vol. 101, no. 14, p. 146402, Oct. 2008.
- [27] K. D. Jöns, P. Atkinson, M. Müller, M. Heldmaier, S. M. Ulrich, O. G. Schmidt, and P. Michler, “Triggered Indistinguishable Single Photons with Narrow Line Widths from Site-Controlled Quantum Dots,” *Nano Lett.*, vol. 13, no. 1, pp. 126–130, Jan. 2013.
- [28] S. Felekyan, R. Kühnemuth, V. Kudryavtsev, C. Sandhagen, W. Becker, and C. A. M. Seidel, “Full correlation from picoseconds to seconds by time-resolved and time-correlated single photon detection,” *Rev. Sci. Instrum.*, vol. 76, no. 8, p. 083104, Aug. 2005.
- [29] R. J. Young, R. M. Stevenson, A. J. Hudson, C. A. Nicoll, D. A. Ritchie, and A. J. Shields, “Bell-inequality violation with a triggered photon-pair source,” *Phys. Rev. Lett.*, vol. 102, no. 3, p. 030406, Jan. 2009.
- [30] T. B. Pittman, B. C. Jacobs, and J. D. Franson, “Heralding single photons from pulsed parametric down-conversion,” *Opt. Commun.*, vol. 246, no. 4–6, pp. 545–550, Feb. 2005.